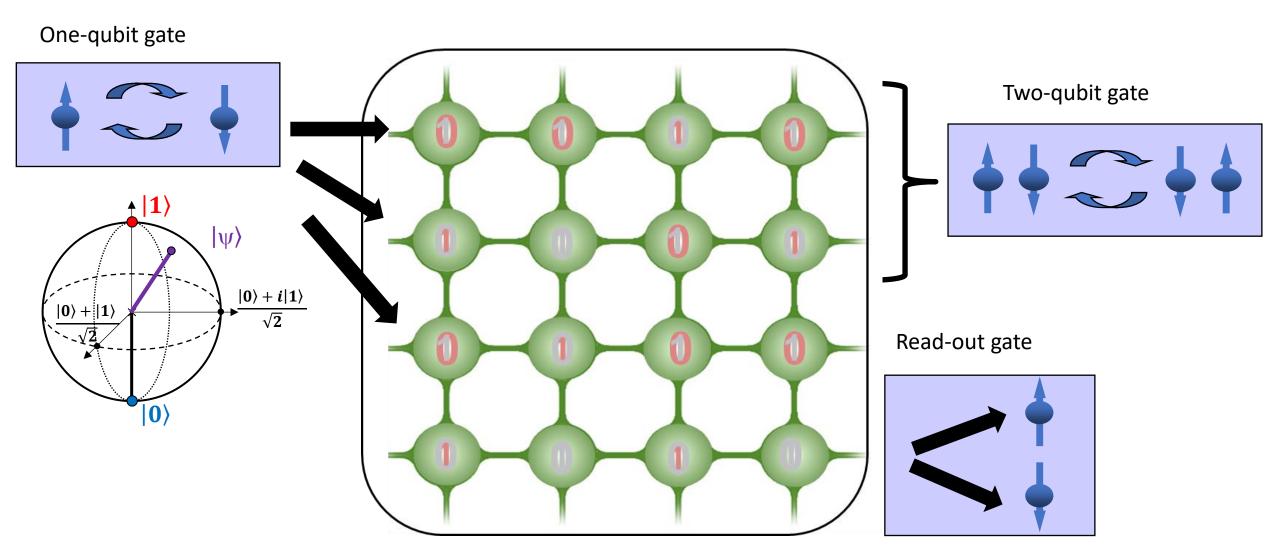


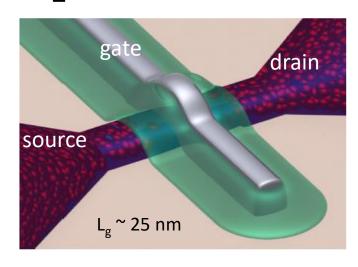
Topology: 2D arrangement and 4 neighbors

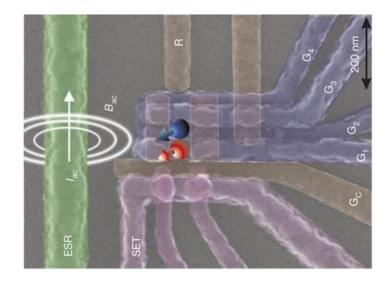


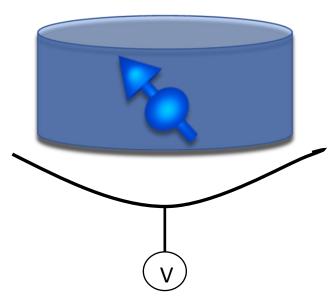
Silicon spin qubits

Si spin

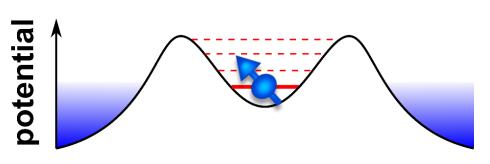
Size	(100nm) ²
Fidelity	>99%
Speed	~1 µs
Manufacturing	
Qubit Variability	0.1%-0.5%
Qubit Turiubility	0.170-0.370
Operation T°	1K
_	







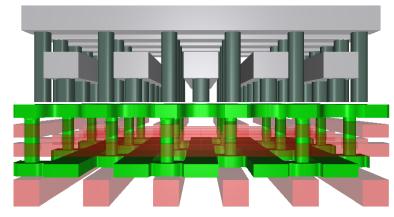
Gate voltage



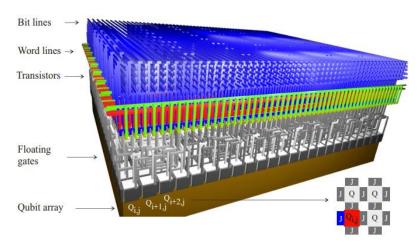
Spin based Quantum computer architectures

Si spin

Size	(100nm) ²
Fidelity	>99%
Speed	~1 µs
Manufacturing	
Qubit Variability	0.1%-0.5%
Operation T°	1K
Connectivity	4
Entangled qubits	12

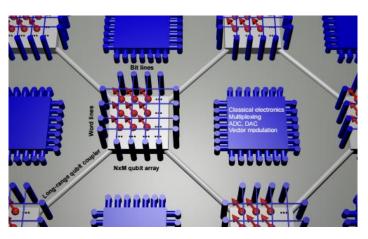


M. Vinet et al et al., IEDM (2018)3D integration of quantum procesor and classical control system



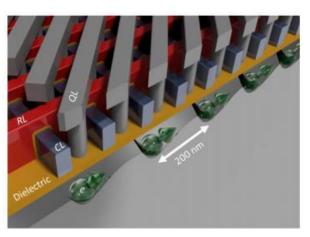
M. Veldhorst et al. (UNSW), Nature Comm. (2017)

10 transistors and 13 control lines per qubit



L.M.K. Vandersypen et al., npj Quant. Inf. (2017)

Monolithic coplanar integration of classical and quantum electronics + long range coupling



R. Li et al., Science express (2017)

Line/column/diagonal addressing of tunnel barriers and QD potentials

Semiconductor industry potential

Good quality qubits

- $\checkmark (100 \text{nm})^2$
- ✓ Coherence time msec
- ✓ Fidelity >99%
- ✓ Speed of operation ~usec

Effective way to control and program these millions of good qubits

Siguance

Computer to control the qubit array

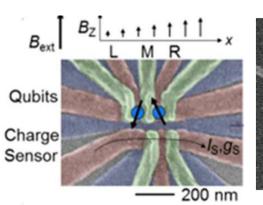


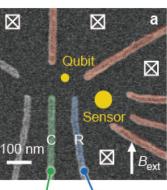


Single chip for control electronics and qubits

Qubit array

The path towards industrialization

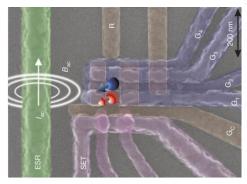


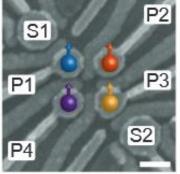


@RIKEN

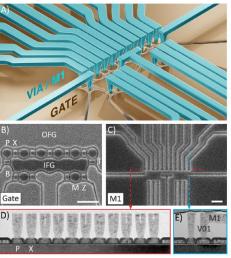
@Princetown

@UNSW

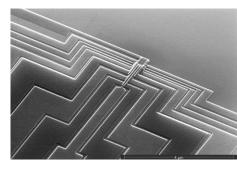




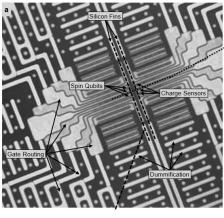




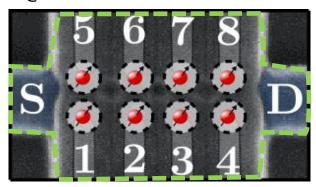
@HRL



@IMEC



@Intel



@Grenoble

Academic fab line,

Wide range of fab protocols for improving qubit performance (ebeam, lift-off)
Many materials (Si, SiGe, Ge)
Many substrates investigated (2DEG, MOS, FinFET, FdSOI)

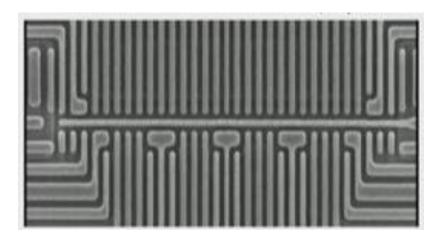
Advanced fab line,

150-300mm tools,
Wide range of fab protocols for improving qubit performance
Focus on Si and SiGe technology
Many substrates investigated (2DEG, MOS, FinFet, FdSOI)

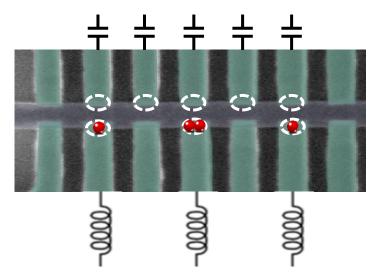
Pre-Industrial fab line,

300mm tools,
Design and material constrains for high yield
Industrial technology
(FdSOI, FinFet only)

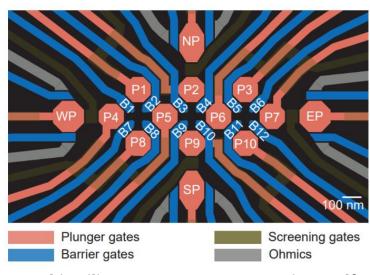
State of art number of qubits



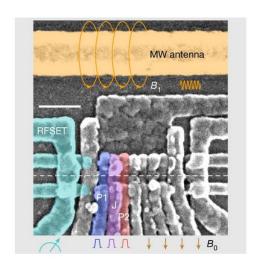
12 qubit linear array (2DEG and Finfet, Tunnel Falls, Intel)



5x2 qubit bilinear array (FDSOI technology, Grenoble)

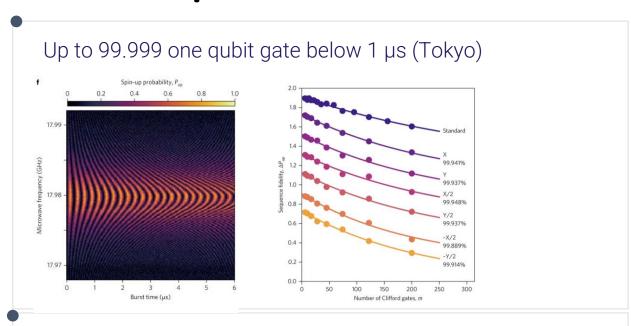


10 qubit trilinear array (2DEG Germanium Delft)

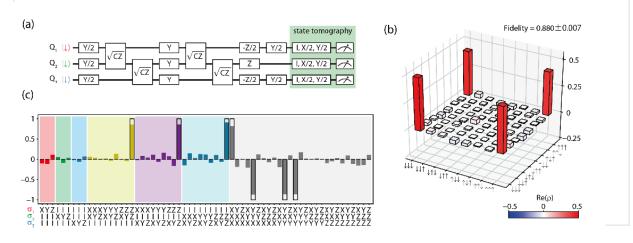


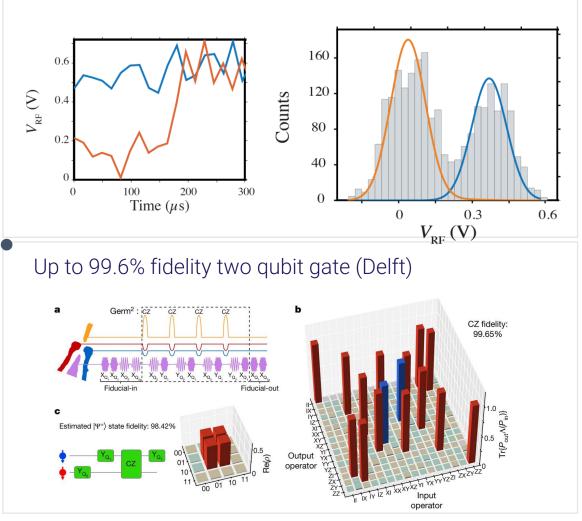
4 qubit linear array (SiMos technology, Sydney)

Few qubit demonstrations



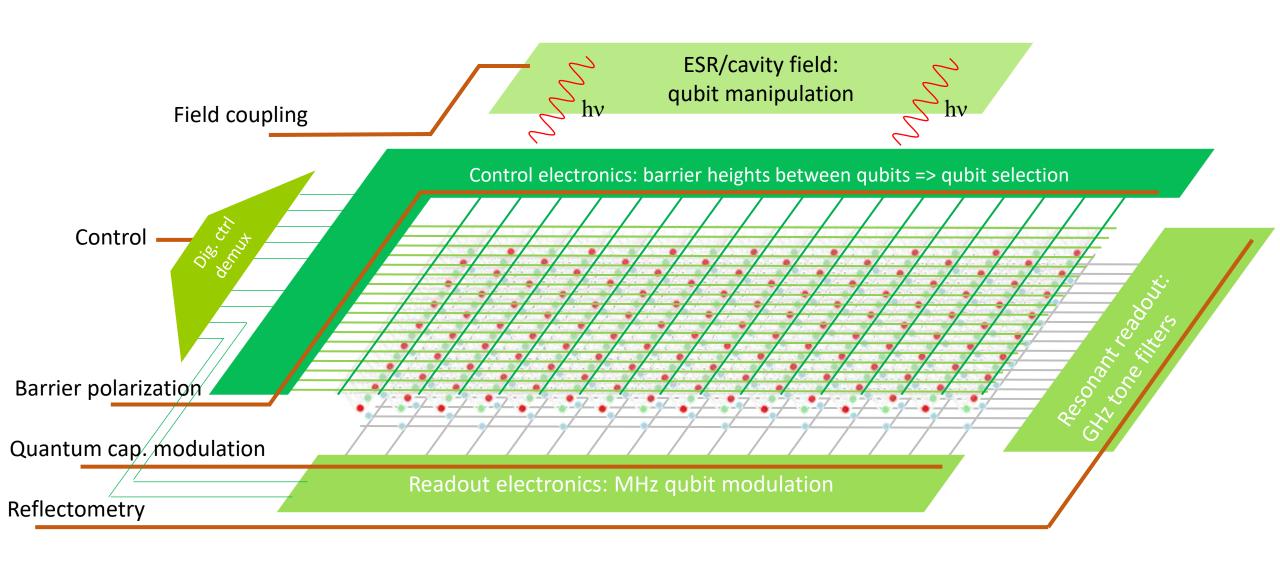




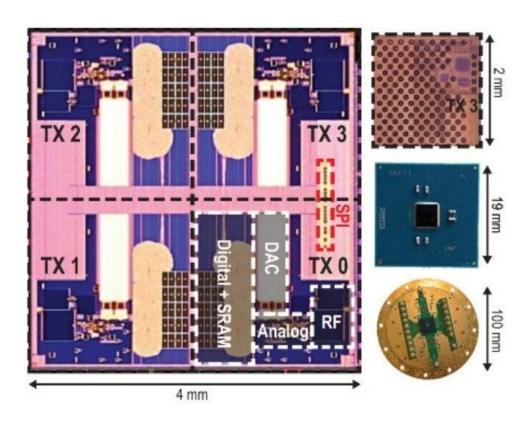


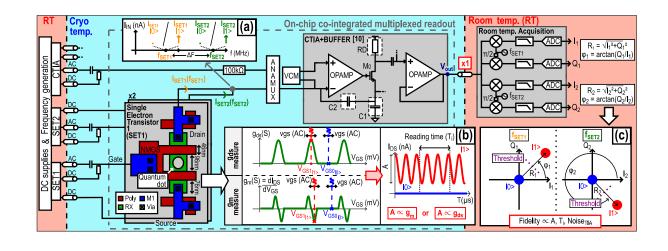
Over 99% single shot spin read-out below 1 µs (Grenoble)

Cryogenic Quantum control architecture



Cryoelectronics developments

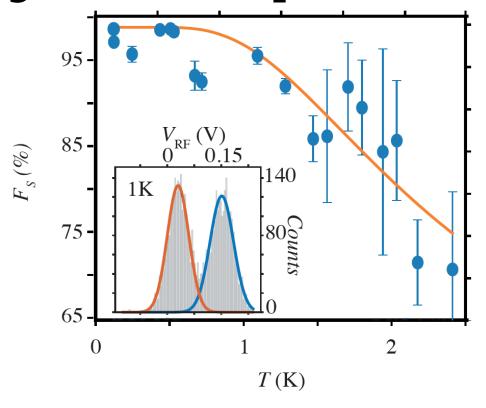




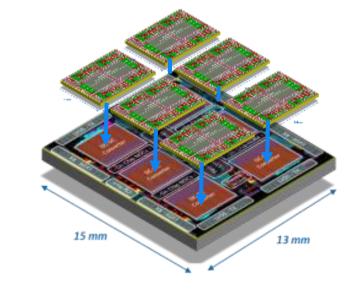
128 qubit control (22nm Intel, Horse ridge, Intel)

Quantum dot co-integrated with amplifier(22FDX and 28FD, Grenoble)

Fidelity Vs Temperature



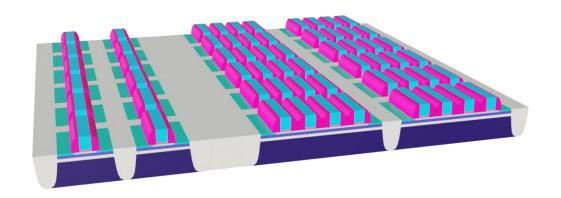
$$\Delta \phi \propto T^{-1} \cosh(aT^{-1})$$



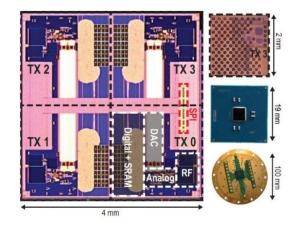
T° of operation	Typical cooling power
30mK	10μW
100mK	100uW
1K	100mW

Urdampilleta et al. Nat. Nanotechnol. (2019).

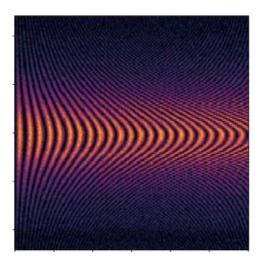
Conclusions and perspectives



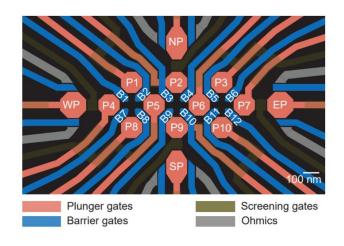
Co integrated Control and quantum hardware



Cryo control



HIFI quantum manipulation



Multi qubit devices